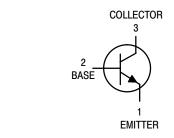
MPS2222A is a Preferred Device

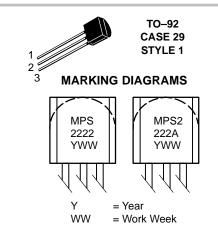
General Purpose Transistors

NPN Silicon



http://onsemi.com





MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MPS2222 MPS2222A	VCEO	30 40	Vdc
Collector–Base Voltage MPS2222 MPS2222A	VCBO	60 75	Vdc
Emitter-Base Voltage MPS2222 MPS2222A	V _{EBO}	5.0 6.0	Vdc
Collector Current – Continuous	IC	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	83.3	°C/W

ORDERING INFORMATION

Device	Package	Shipping
MPS2222	TO-92	5000 Units/Box
MPS2222A	TO-92	5000 Units/Box
MPS2222ARLRA	TO-92	2000/Tape & Reel
MPS2222ARLRM	TO-92	2000/Ammo Pack
MPS2222ARLRP	TO-92	2000/Ammo Pack
MPS2222RLRA	TO-92	2000/Tape & Reel
MPS2222RLRM	TO-92	2000/Ammo Pack
MPS2222RLRP	TO-92	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		'		•	•
Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	MPS2222 MPS2222A	V _(BR) CEO	30 40	_ _	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu Adc, I_E = 0$)	MPS2222 MPS2222A	V(BR)CBO	60 75	_ _	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	MPS2222 MPS2222A	V _{(BR)EBO}	5.0 6.0	_ _	Vdc
Collector Cutoff Current (VCE = 60 Vdc, VEB(off) = 3.0 Vdc)	MPS2222A	ICEX	_	10	nAdc
Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0) (V _{CB} = 60 Vdc, I _E = 0) (V _{CB} = 50 Vdc, I _E = 0, T _A = 125°C) (V _{CB} = 50 Vdc, I _E = 0, T _A = 125°C)	MPS2222 MPS2222A MPS2222 MPS2222A	ICBO	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (VEB = 3.0 Vdc, I _C = 0)	MPS2222A	IEBO	_	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MPS2222A	I _{BL}	-	20	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_{C} = 0.1 \text{ mAdc, } V_{CE} = 10 \text{ Vdc}) \\ &(I_{C} = 1.0 \text{ mAdc, } V_{CE} = 10 \text{ Vdc}) \\ &(I_{C} = 10 \text{ mAdc, } V_{CE} = 10 \text{ Vdc}) \\ &(I_{C} = 10 \text{ mAdc, } V_{CE} = 10 \text{ Vdc, } T_{A} = -55^{\circ}\text{C}) \\ &(I_{C} = 150 \text{ mAdc, } V_{CE} = 10 \text{ Vdc) (Note 1.)} \\ &(I_{C} = 150 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc) (Note 1.)} \\ &(I_{C} = 500 \text{ mAdc, } V_{CE} = 10 \text{ Vdc) (Note 1.)} \end{aligned} $	MPS2222A only MPS2222 MPS2222A	hFE	35 50 75 35 100 50 30 40	- - - 300 - -	-
Collector–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc)	MPS2222 MPS2222A	VCE(sat)	- -	0.4 0.3	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MPS2222 MPS2222A		- -	1.6 1.0	
Base–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc)	MPS2222 MPS2222A	V _{BE} (sat)	- 0.6	1.3 1.2	Vdc
$(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MPS2222 MPS2222A		- -	2.6 2.0	

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic			Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTIC	CS		•			1
Current–Gain – Bandwidth Product (Note (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100	,	MPS2222 MPS2222A	fΤ	250 300	_ _	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E =	0, f = 1.0 MHz)		C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		MPS2222 MPS2222A	C _{ibo}	- -	30 25	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 I		MPS2222A MPS2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kg.)		MPS2222A MPS2222A	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 kg.)		MPS2222A MPS2222A	h _{fe}	50 75	300 375	-
Output Admittance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 1.0 H		MPS2222A MPS2222A	h _{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (IE = 20 mAdc, V _{CB} = 20 Vdc, f = 31.8	MHz)	MPS2222A	rb′C _C	-	150	ps
Noise Figure $(I_{C}=100~\mu\text{Adc, V}_{CE}=10~\text{Vdc, R}_{S}=1.0~\text{k}\Omega,f=1.0~\text{kHz})$ MPS2222A		NF	-	4.0	dB	
SWITCHING CHARACTERISTICS	MPS2222A only					
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc},$ $I_{C} = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc}) \text{ (Figure 1)}$		td		10	ns
Rise Time			t _r	-	25	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc}, I_{B1} = I_{B2} = 15 \text{ mAdc})$ (Figure 2)		t _S	-	225	ns
Fall Time			t _f	-	60	ns

^{2.} f_T is defined as the frequency at which $|h_{\mbox{\scriptsize fe}}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

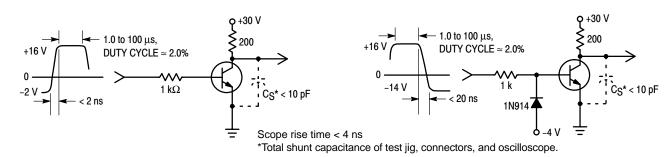


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

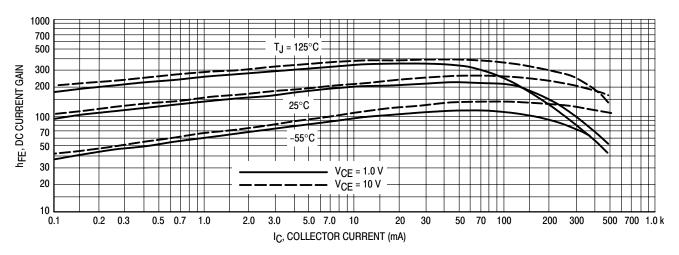


Figure 3. DC Current Gain

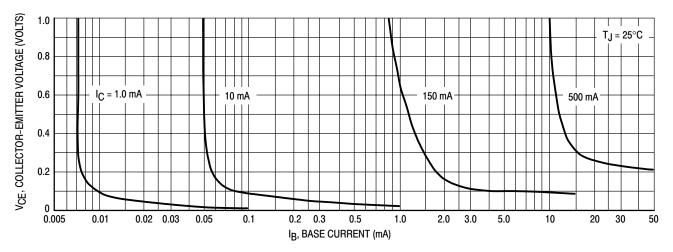


Figure 4. Collector Saturation Region

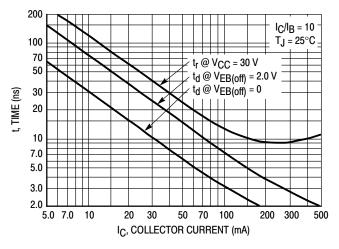


Figure 5. Turn-On Time

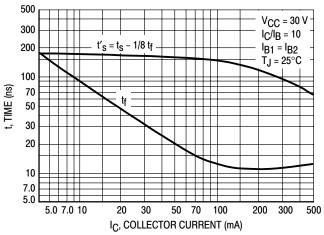


Figure 6. Turn-Off Time

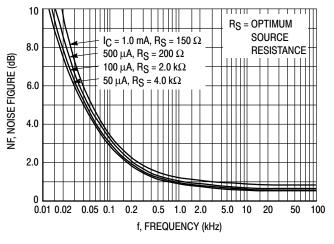


Figure 7. Frequency Effects

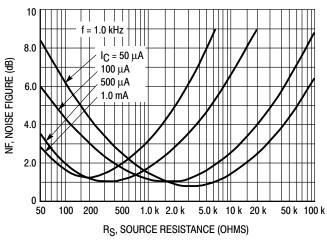


Figure 8. Source Resistance Effects

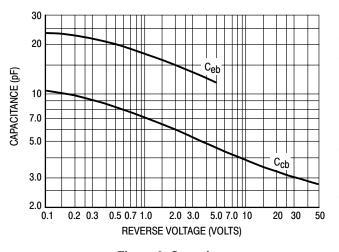


Figure 9. Capacitances

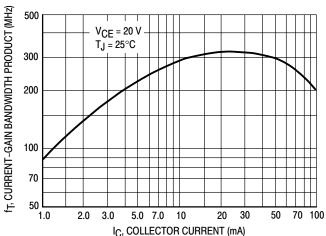
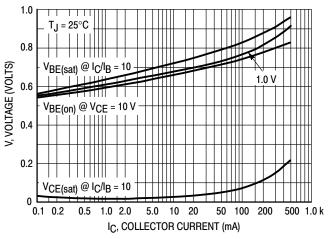


Figure 10. Current-Gain Bandwidth Product





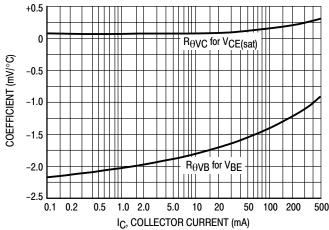
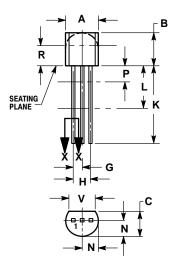


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 **TO-226AA** CASE 29-11

ISSUE AL





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0 135		3 43	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

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